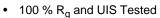


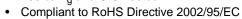
N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)	
30	$0.045 \text{ at V}_{GS} = 10 \text{ V}$	15 ^d	21.7	
	0.058 at V _{GS} = 4.5 V	15 ^d	21.7	

FEATURES



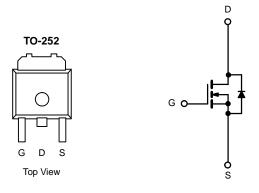






APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- DC/DC Converter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_C = 25 ^{\circ}C$, unless other	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	1-	15 ^d	A	
Continuous Diain Guiterit (1) = 130 °C)	T _C = 70 °C		15 ^d		
Pulsed Drain Current		I _{DM}	100	A	
Avalanche Current		I _{AS}	40		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	80	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	В	59.5 ^b	· w	
	T _A = 25 °C ^c	P _D	2.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	46	- °C/W	
Junction-to-Case (Drain)	R _{thJC}	2.1		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.c. When mounted on 1" square PCB (FR-4 material).
- d. Package limited.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		2.5	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current		V _{DS} = 30 V, V _{GS} = 0 V			1	
	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α
	В	V _{GS} = 10 V, I _D = 12 A		0.037	0.045	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		0.055	0.058	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		110		S
Dynamic ^b						
Input Capacitance	C _{iss}			2780		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz		641		
Reverse Transfer Capacitance	C _{rss}			260		
Total Gate Charge ^c	Qg	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		44	66	
Total Gate Charge				21.7	32.6	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$		7		
Gate-Drain Charge ^c	Q_{gd}			6.7		
Gate Resistance	R _g	f = 1 MHz	0.4	2	4	Ω
Turn-On Delay Time ^c	t _{d(on)}			8	16	
Rise Time ^c	t _r	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		9	18	ns
Turn-Off Delay Time ^c	t _{d(off)}			35	53	
Fall Time ^c	t _f			9	18	
Drain-Source Body Diode Ratings a	nd Characteris	stics T _C = 25 °C ^b		•	•	
Continuous Current	I _S				50	۸
Pulsed Current	I _{SM}				100	_ A
Forward Voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V		0.75	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 10 A, dl/dt = 100 A/μs		34	51	ns
Peak Reverse Recovery Current	I _{RM(REC)}			2	3	Α
Reverse Recovery Charge	Q _{rr}			34	51	nC

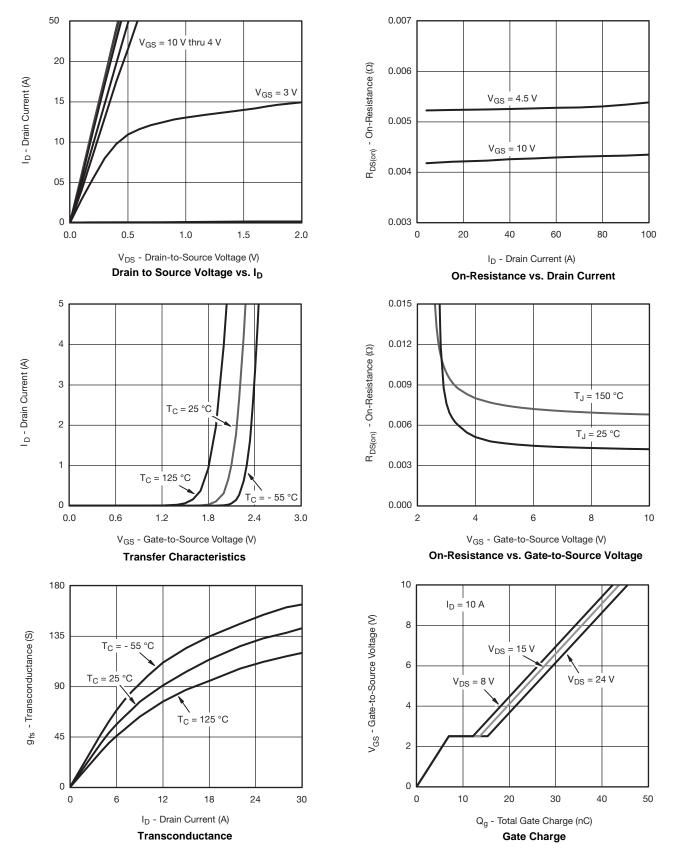
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

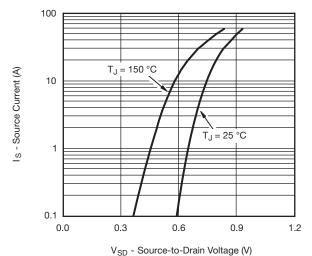


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

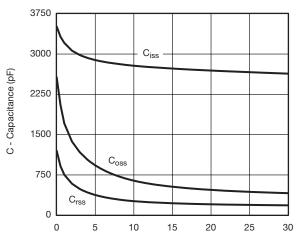




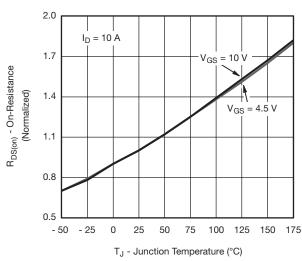
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



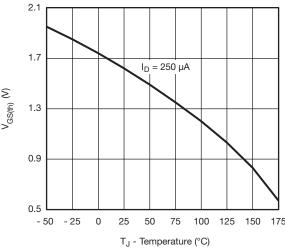
Source-Drain Diode Forward Voltage



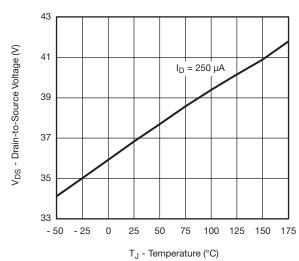
 V_{DS} - Drain-to-Source Voltage (V) $\label{eq:capacitance}$



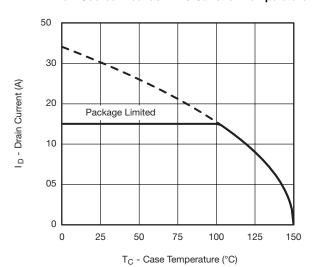
On-Resistance vs. Junction Temperature



Threshold Voltage

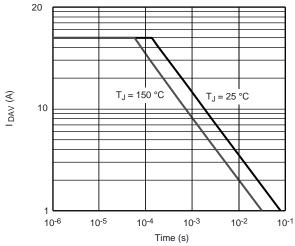


Drain Source Breakdown vs. Junction Temperature

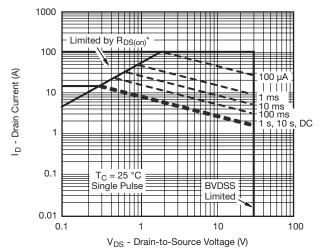


Current Derating

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

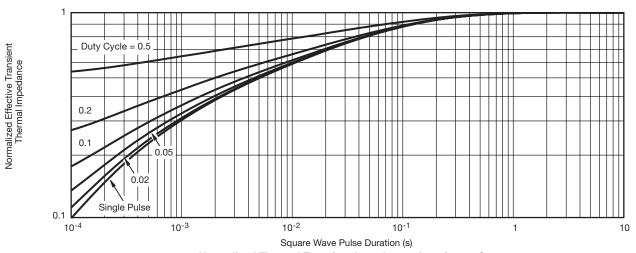


Single Pulse Avalanche Current Capability vs. Time



 * V $_{GS}$ > minimum V $_{GS}$ at which R $_{DS(on)}$ is specified





Normalized Thermal Transient Impedance, Junction-to-Case

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